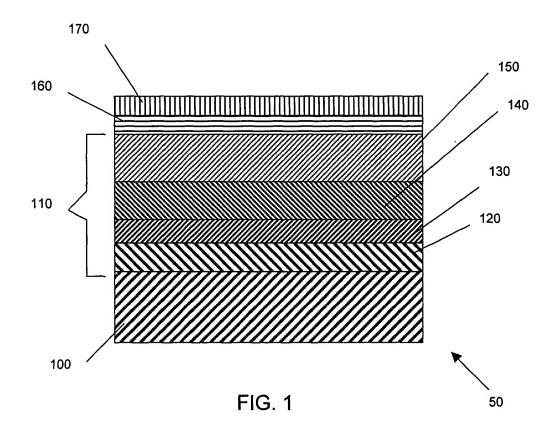
Title: SEMICONDUCTOR HETEROSTRUCTURES AND RELATED METHODS
Inventors: Leitz et al.
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Atty Docket No.: ASC-058A
Attorney for Applicants: Mark L. Beloborodov
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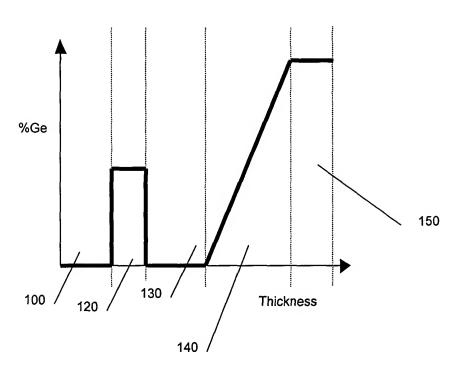


FIG. 2

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	Qualitative Evaluation of Dislocation Pile-Up D nsity			
% Ge	$H^* = 0.6 T_{crit}$	$H = 1.25 T_{crit}$	$H = 2 T_{crit}$	$H = 5 T_{crit}$
5	High	Medium	Low	Low
10	High	Medium	Medium	Low
15	High	Medium	Medium	Low

^{*} Thickness (H) of the Seed Layer Relative to Its Critical Thickness (T_{crit}).

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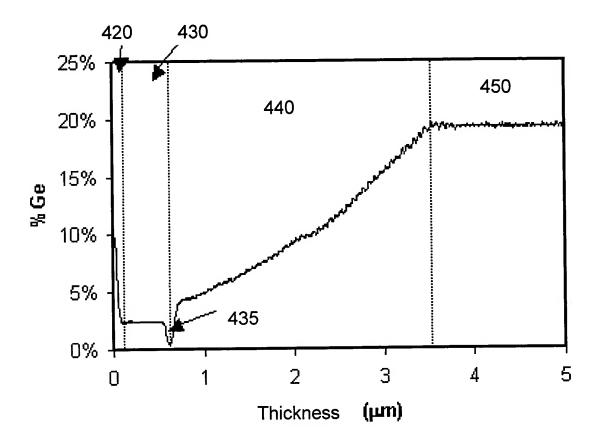


FIG. 4

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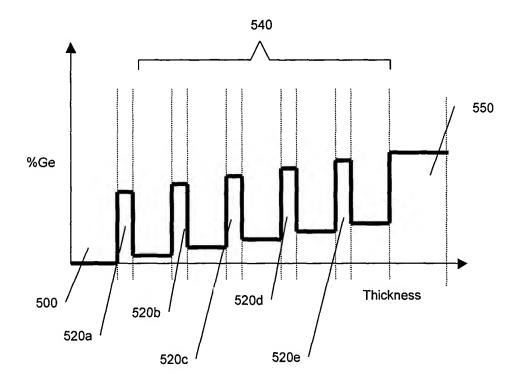


FIG. 5

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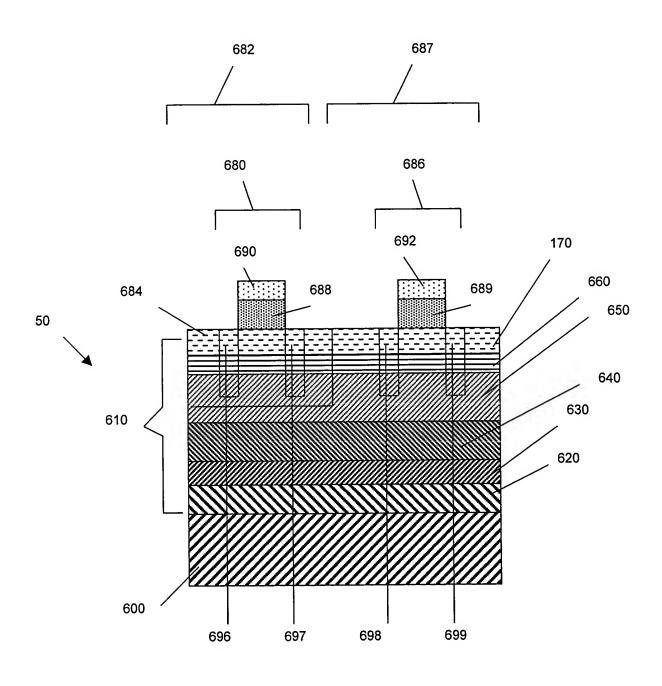


FIG. 6